

Silicon NPN Power Transistors

2SC3026

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- High voltage power switching character
- display horizontal deflection output

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

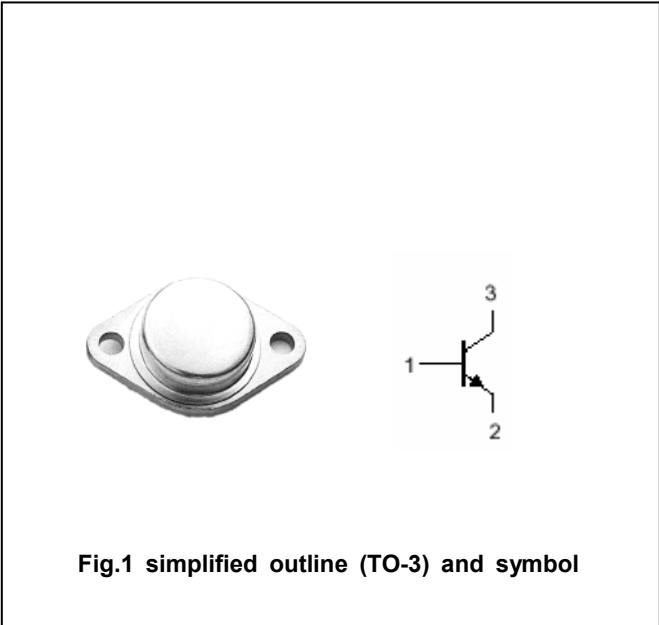


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1700	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CP}	Collector current-peak		6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-45~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; R _{BE} =∞	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	6			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =5A; I _B =1.25A			2.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =5A; I _B =1.25A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1700V; R _{BE} =∞			0.5	mA

Switching times

t _s	Storage time	I _C =5A; I _{B1} =1A; I _{B2} =-2.5A		4.0		μs
t _f	Fall time				0.5	μs

PACKAGE OUTLINE

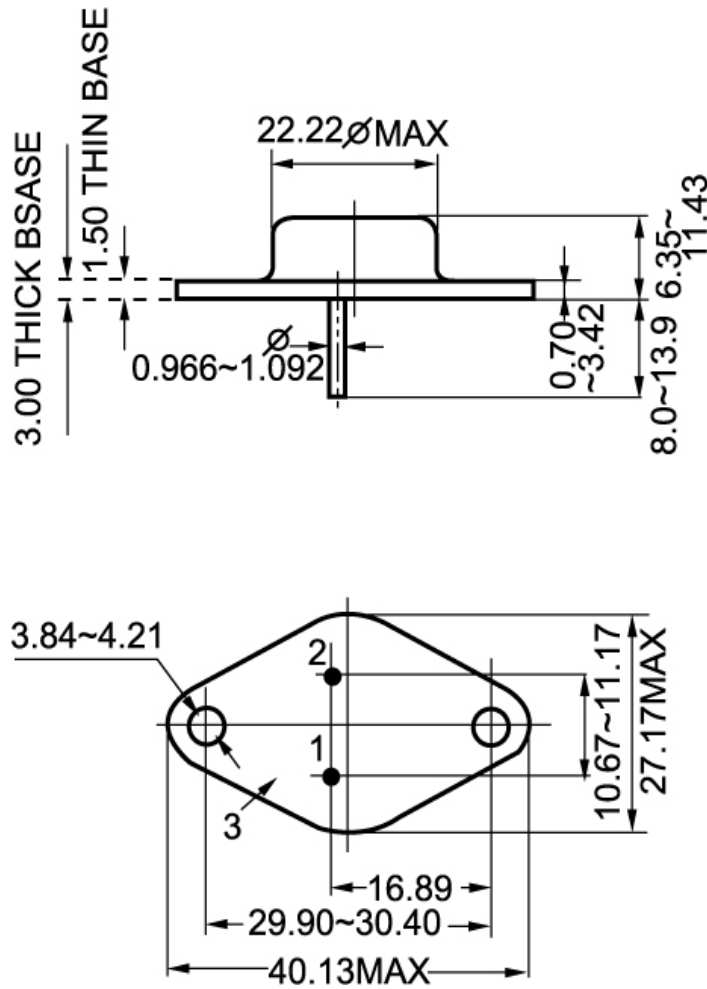


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)